

All-optical ultrafast switching of Si woodpile photonic band gap crystals

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Abstract

We present ultrafast all-optical switching measurements of Si woodpile photonic band gap crystals at telecom frequencies. The crystals are homogeneously excited by a two-photon process. We probe the switching by measuring reflectivity over broad frequency ranges as a function of time. At short delay times, we observe that the photonic gap becomes narrower than in the unswitched case. After 1 ps, the complete gap has shifted to higher frequencies. This intricate behavior is the result of competing refractive index changes due to the electronic Kerr effect and to optically excited free carriers. The frequency shift of the band gap as a function of pump intensity agrees well with Fourier modal method calculations with no freely adjustable parameters.

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Currently many efforts are devoted to a novel class of dielectric composites known as photonic crystals [1]. Spatially periodic variations of the refractive index commensurate with optical wavelengths cause the photon dispersion relation to organize in bands, analogous to electron bands in solids. Generally, frequency windows known as stop gaps appear in which modes are forbidden for specific propagation directions. Fundamental interest in photonic crystals is spurred by the possibility of a photonic band gap, a frequency range for which no modes exist at all. Tailoring of the photonic density of states by a photonic crystal allows one to control fundamental atom-radiation interactions in solid-state environments [2, 3]. In this context the hallmark of a photonic band gap is the eagerly awaited full inhibition of spontaneous emission due to a vanishing density of states [2]. Additional interest is aroused by the possibility of Anderson localization of light by defects added to photonic band gap crystals [4].

Exciting prospects arise when photonic band gap crystals are switched on ultrafast timescales. In particular, switching photonic band gap crystals provides dynamic control over the density of states that would allow the switching-on or -off of light sources in the band gap [5]. Furthermore, switching would allow the capture or release of photons from photonic band gap cavities [5], which is relevant to solid-state slow-light schemes [6]. Switching directional properties of photonic crystals also leads to fast changes in the reflectivity, where interesting changes have been reported for Bragg stacks [7, 8], 2D photonic crystals [9, 10], and first-order stop bands of 3D self-assembled crystals [11, 12]. Ultrafast control of the propagation of light is essential to applications in active photonic integrated circuits [13].

In this Letter, we present ultrafast all-optical switching measurements of Si woodpile photonic band gap crystals at telecom frequencies. The crystals are homogeneously excited by a two-photon process. We probe the switching by measuring reflectivity over broad frequency ranges as a function of time. At short delay times < 200 fs, we observe that the photonic gap becomes narrower than in the unswitched case. After 1 ps, the complete gap has shifted to higher frequencies. This intricate behavior is the result of competing refractive index changes due to the electronic Kerr effect and to optically excited free carriers. Our experiments are compared to Fourier modal method calculations with no freely adjustable parameters [14]. The measured and calculated frequency shift of the band gap as a function of pump intensity are found to agree well.

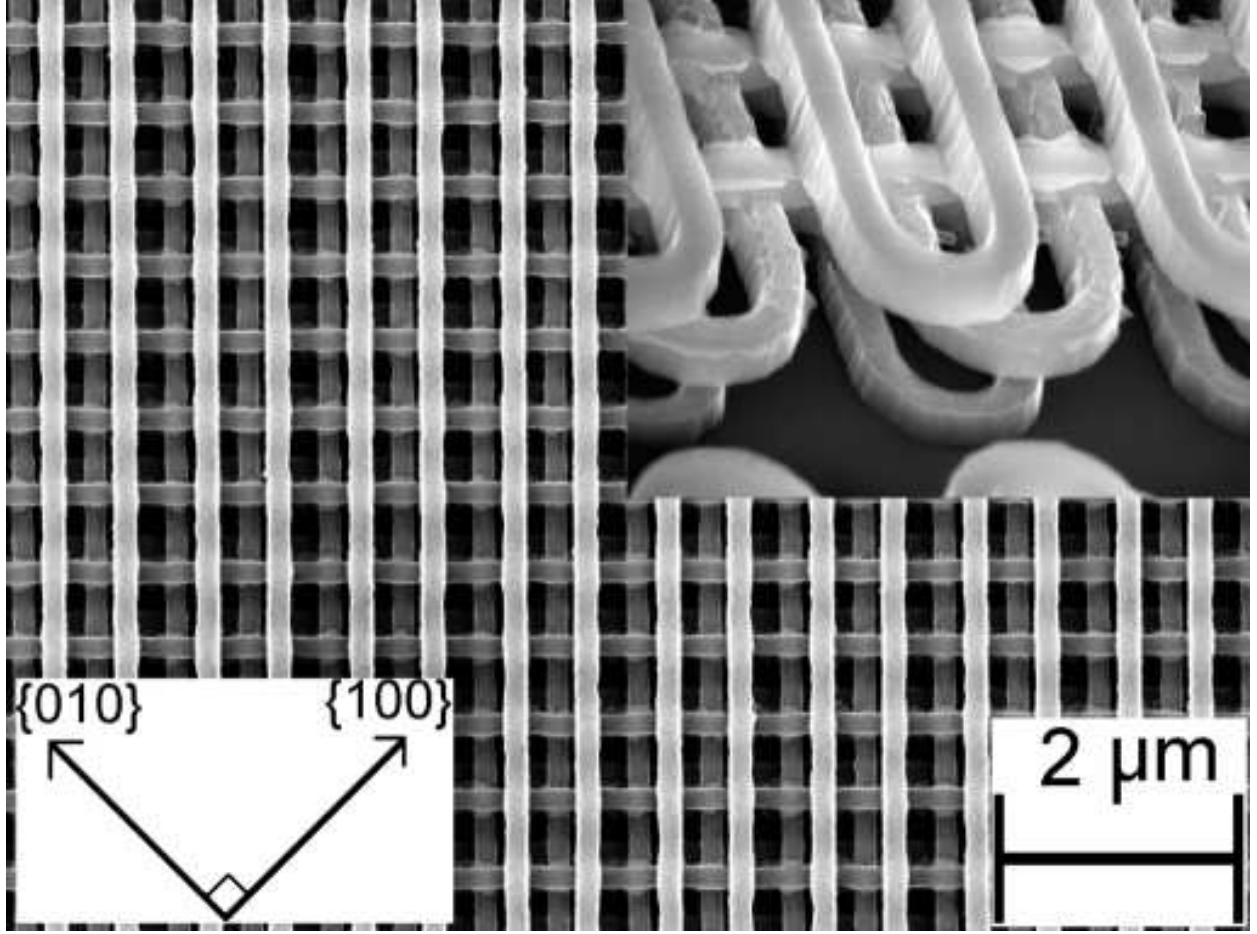


FIG .1: High resolution scanning electron micrographs of a (001) surface of a Si woodpile crystal. The average lateral distance between two consecutive rods is 650 ± 10 nm . The arrows indicate the (010) and the (100) direction of the woodpile crystal. Inset: side view of the crystal. The width and thickness of each rod is 175 ± 10 nm and 155 ± 10 nm respectively.

The Si woodpile photonic crystals are made using a layer-by-layer approach and are designed to have a photonic band gap around the telecommunication wavelength of $1.55 \mu\text{m}$ [15, 16]. The crystals consist of five layers of stacked polycrystalline Si nanorods that have a refractive index of 3.45 at $1.55 \mu\text{m}$. High resolution scanning electron micrographs of a crystal are shown in Fig. 1. While each second rod in the crystal is slightly displaced by 50 nm , this periodic perturbation and the resulting superstructure do not affect the photonic band gap region [17]. Our measurements were reproduced on multiple different crystals.

A successful optical switching experiment requires an as large as possible switching magnitude, ultrafast time-scales, as low as possible induced absorption, as well as good spatial

homogeneity [5]. In Si woodpile photonic crystals, optimum switching conditions are obtained for pump frequencies near the two-photon absorption edge of Si $\approx 5000 \text{ cm}^{-1}$ ($\approx 2000 \text{ nm}$) [18]. Switching experiments at such low pump frequencies require a laser system that produces pulses with intensities of up to 100 GW cm^{-2} . The setup used in our experiments consists of a regeneratively amplified Ti:Saph laser (Spectra Physics Hurricane) which drives two independently tunable optical parametric amplifiers (OPA, Topas). The OPAs have a continuously tunable output frequency between 3850 and 21050 cm^{-1} , with pulse durations of 150 fs and a pulse energy E_{pulse} of at least 20 J . The maximum pump intensities that can be achieved in this setup exceed 1 TW cm^{-2} , sufficient for our switching experiments. The E-field of the probe beam is polarized along the (-110) direction of the crystal, incident at normal incidence $\theta = 0^\circ$, and is focused to a Gaussian spot of $24 \text{ }\mu\text{m}$ FWHM at a small numerical aperture $\text{NA} = 0.02$. The pump beam is incident at $\theta = 15^\circ$, and has a much larger Gaussian focus of $113 \text{ }\mu\text{m}$ FWHM than the probe, providing good lateral spatial homogeneity. We ensure that only the central part of the pump focus is probed. The reflectivity was calibrated by referencing to a gold mirror. A versatile measurement scheme was developed to subtract pump background from the probe reflectance signal, and to compensate for possible pulse-to-pulse intensity variations in the output of our laser [19].

Linear reflectivity measurements of the crystal are presented as open squares in Fig. 2. The broad stop band from 5600 to 8800 cm^{-1} corresponds to the Γ -X stop gap in the band structure, which is part of the 3D photonic band gap of Si woodpile photonic crystals [14, 15]. The large width confirms that the crystals interact strongly with the light, confirming band gap behavior. While the crystals are relatively thin, the strong interaction and the excellent crystal quality result in the high reflectivity of 95% . For comparison, Si inverse opal photonic structures have typically lower reflectivity. The small discontinuities in the spectrum appear at the limits of the scanning range of the different signal types of our OPA and are probably due to a slight beam walk off. The OPA spectra were well reproduced on different positions on the crystal surface and with a white light spectrometry setup. The dashed curve in Fig. 2 represents an Fourier modal method calculation of the reflectivity in the (001) direction [14]. The measured Si rod dimensions, the displacements of individual layers, as well as the superstructure were included in our model. The good agreement between our measurements and the theory is remarkable since no parameters were freely adjusted, and in view of

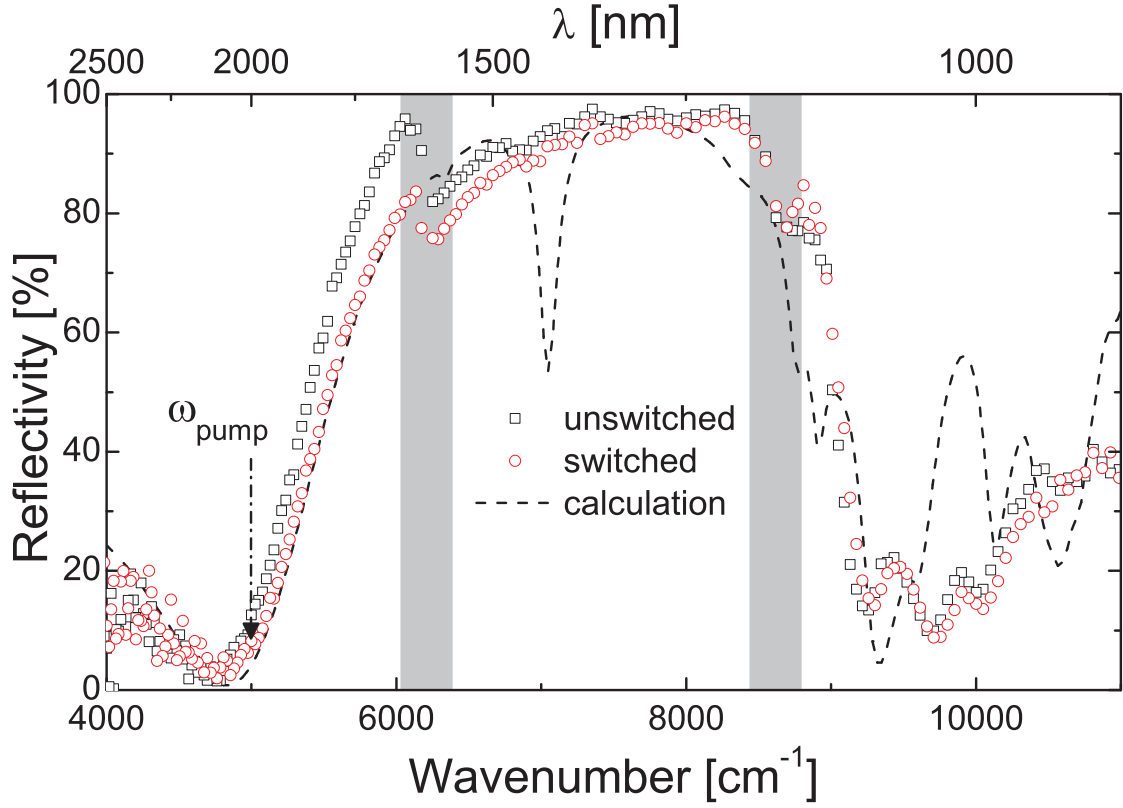


FIG. 2: (color online) Linear (squares) and switched (circles) reflectivity spectra measured in the (001) direction. A broad stop band with a maximum reflectivity of 95% appears for frequencies between 5640 cm^{-1} and 8840 cm^{-1} . The gray areas indicate the edges of the scanning ranges of our OPA. The arrow indicates the pump frequency $\omega_{\text{pump}} = 5000 \text{ cm}^{-1}$. The pump peak intensity was $I_0 = 26 \text{ GW cm}^{-2}$ on the red part, $I_0 = 28 \text{ GW cm}^{-2}$ on the central part, and $I_0 = 26 \text{ GW cm}^{-2}$ on the blue part of the spectrum. The switched spectra were measured at a pump-probe time delay of 1 ps on the red part, 300 fs on the central part and 1.5 ps on the blue part of the spectrum. The dashed curve represents an Fourier modal method calculation that agrees well with the linear measurements in the band gap region.

averaging over the laser bandwidth.

In Fig. 2, the red circles show the reflectivity 1.5 ps after switching the crystal with a laser pulse with peak intensity $I_0 = 28 \text{ GW cm}^{-2}$. This spectrum clearly reveals that the complete spectrum is blue-shifted by as much as 120 cm^{-1} , with decreases on the red edge

and increases on the blue edge of the gap. The high reactivity in the gap confirms that the induced absorption is low, and thus that the switched crystal remains transparent, as opposed to some previous results [11]. From I_0 and the two-photon absorption coefficient $\beta = 0.2 \text{ cm GW}^{-1}$ [20], we deduce a large pump absorption length $\ell_{\text{pump}} = 1/I_0 = 0.18 \text{ cm}$, or 2600 lattice spacings. This result confirms that two-photon absorption yields much more homogeneously switched crystals than one-photon absorption [18].

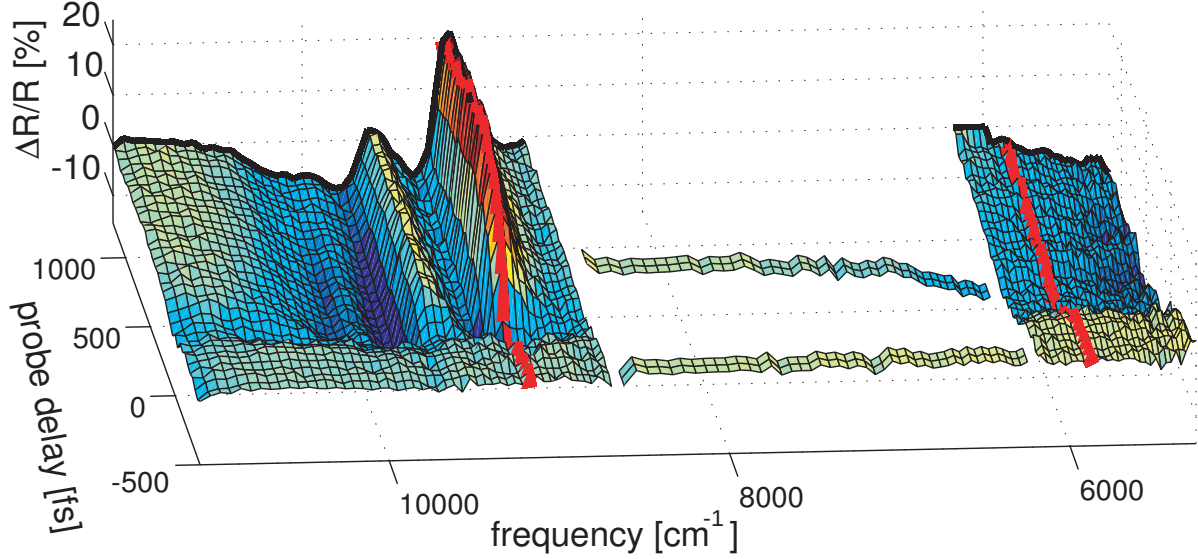


FIG. 3: (color) Differential reactivity as a function of both probe frequency and probe delay. The probe delay was varied from -500 to 1250 fs in steps of $\Delta t = 50$ fs. The probe wavelength was tuned from 1620 to 1900 nm in $\Delta \lambda = 10$ nm steps in the low-frequency range, from 1160 to 1600 nm in the central range, and from 900 nm to 1150 nm in 5 nm steps in the high-frequency range. The pump intensity was $I_0 = 27 \text{ GW cm}^{-2}$ on the red part, $I_0 = 28 \text{ GW cm}^{-2}$ on the central part, and $I_0 = 29 \text{ GW cm}^{-2}$ on the blue part. In the central part of the stop band, $R/R(!)$ was measured at both negative delays and a delay of 300 fs. The red curves indicate fixed frequency curves along which delay traces were measured at both short and long delays, see Fig. 4

The independent tunability of our probe laser allows to for the first time scan the reactivity spectrum as a function of frequency at a chosen time delay after the pump pulse. The temporal evolution at ultrafast time scales of the differential reactivity of the crystal R/R is represented as a three-dimensional surface plot in Fig. 3 as a function of time delay and probe frequency. At low frequencies near 6000 cm^{-1} , the reactivity displays an

ultrafast decrease $R/R = -8\%$ indicative of a shift of the red edge of the stop band to higher frequencies. At intermediate frequencies near 7000 cm^{-1} , the peak reactivity of the stop band decreases by less than $R/R = -1\%$, confirming that the induced absorption in the structure is small. At high frequencies $> 8000 \text{ cm}^{-1}$, we observe intricate temporal behavior: near zero delay, a brief 200 fs decrease in reactivity ($R/R = -5\%$) is followed by either a further decrease or by a strong increase up to $R/R = 25\%$, depending on λ . The decrease at zero delay is attributed to the electronic Kerr effect, and was used to correct our temporal calibration for dispersion in the probe path. The decrease followed by an increase at 9170 cm^{-1} indicates that the photonic gap becomes narrow at short times, followed by a blue shifting of the complete gap at longer times. At probe frequencies near 9400 cm^{-1} , strong variations in R/R with frequency are related to the shift of the superstructure feature at $\lambda = 9400 \text{ cm}^{-1}$ (see Fig. 2), and provide additional evidence of a large change in refractive index.

To study the intricate ultrafast behavior in more detail, we have measured time traces at two characteristic frequencies, namely the red and blue edge of the stop band, that are indicated by the red traces in Fig. 3. The time delay curves of the calibrated absolute reactivity change R in Fig. 4 are measured over an extended range. At the blue edge, a rapid decrease to $R = -1\%$ appears within 190 fs, followed after 80 fs by an increase to $R = 5\%$ within 500 fs. The effect decays exponentially with a decay time of 18 ± 1 ps. The reactivity at the red edge decreases by $R = -12\%$ within 1 ps. At delay times longer than 2.5 ps after the excitation, the effect on the red edge decays exponentially to $R = -1\%$ with a decay time of 16 ± 2 ps. The decay times of about 18 ps are much faster than carrier relaxation times in bulk Si, likely since our photonic crystals are made of a poly-crystalline material, in which lattice defects and grain boundaries act as efficient carrier recombination traps [22]. This relatively fast decay time implies that switching could potentially be repeated at a rate above 25 GHz, which is relevant to possible future switching and modulation applications.

The measured frequency shift of the blue edge of the stop band at 9100 cm^{-1} is plotted versus peak pump power squared I_0^2 in figure 5. We have also plotted the frequency shift of the reactivity feature at 9750 cm^{-1} . Both features shift approximately linearly with the peak pump power squared, which confirms that two-photon absorption is indeed the dominant excitation mechanism. A large maximum shift of the stop band edge $\lambda = \lambda =$

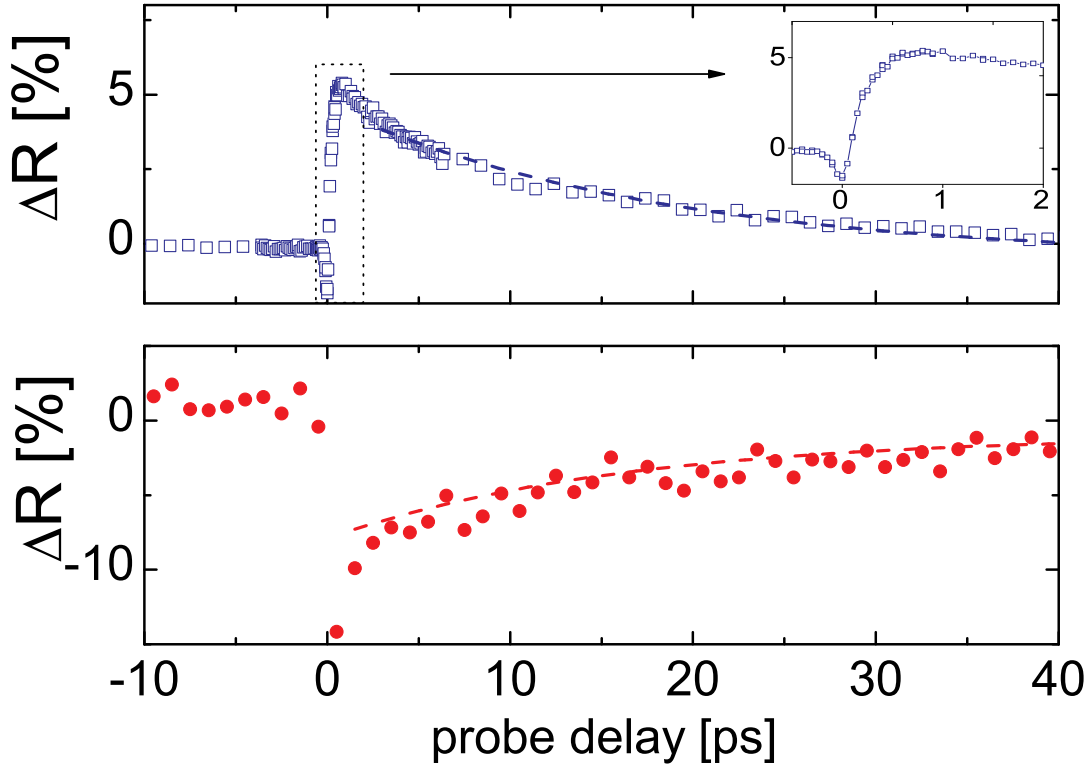


FIG . 4: (color online) Absolute reflectivity changes versus probe delay at probe frequency $\omega_{\text{blue}} = 9174 \text{ cm}^{-1}$ at the blue edge of the gap, $I_0 = 32 \text{ GW cm}^{-2}$ (upper panel) and $\omega_{\text{red}} = 5882 \text{ cm}^{-1}$ at the red edge of the gap, $I_0 = 34 \text{ GW cm}^{-2}$ (lower panel). The dashed curves are exponential fits with a decay time of 18 ps (upper panel) and 16 ps (lower panel).

0.54% is observed. The measured shifts were compared to Fourier modal method theory that includes two-photon absorption. The optical properties of Si are described by the Drude model, which is valid for electron densities in the range of our experiments $N_{\text{eh}} = 1.5 \cdot 10^{19} \text{ cm}^{-3}$ [23]. We find good agreement between our measurements and the theory in particular since no parameters were adjusted. We deduce a large maximum change in refractive index $\Delta n = n_{\text{Si}} = 0.7\%$ in the Si backbone. The physical interpretation of diamond-like structures, in which the photonic band gap appears in the first order stop gap region, is much simpler compared to Si inverse opals where the band gap is expected in the range of second order Bragg diffraction where complex multiple Bragg wave coupling must be taken

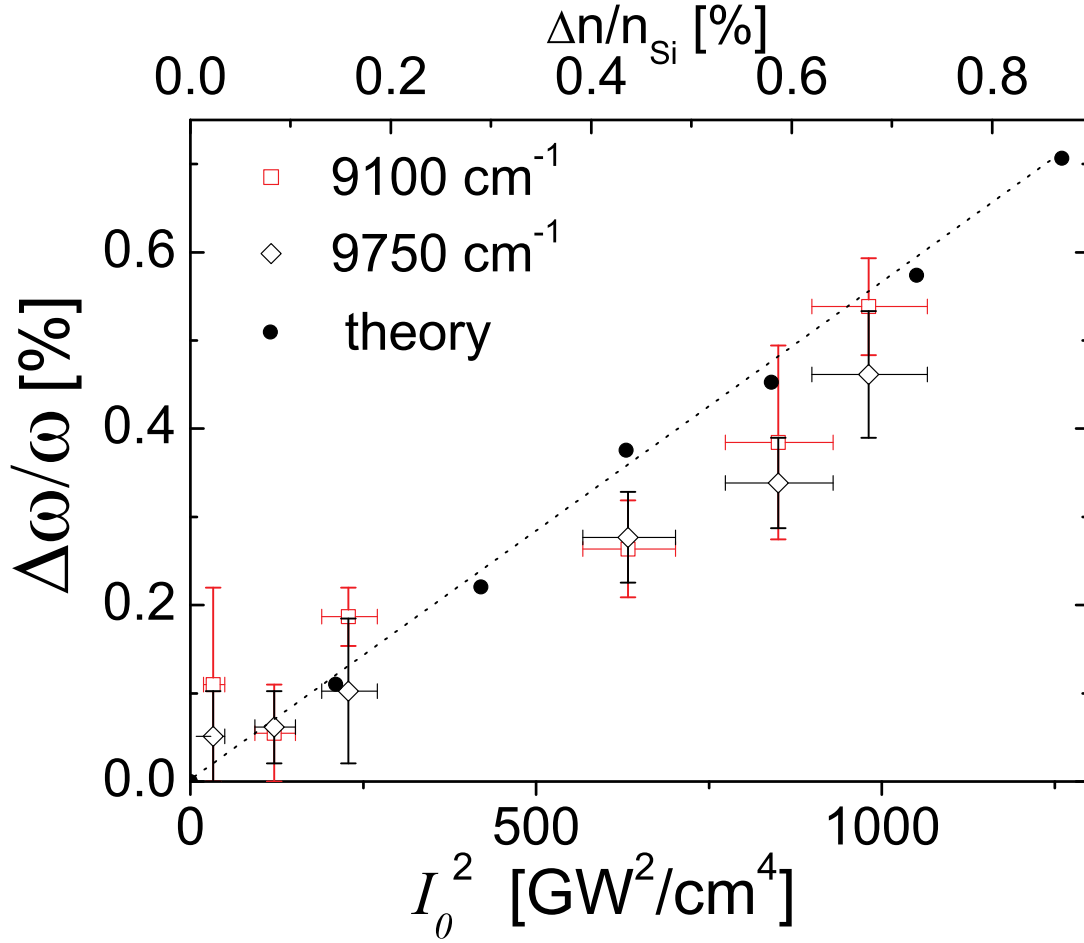


FIG. 5: (color online) Squares: measured shift $\Delta\omega/\omega$, at $\omega = 9100$ cm⁻¹ on the blue edge of the stop band versus I_0^2 . Diamonds: $\Delta\omega/\omega$ measured at $\omega = 9750$ cm⁻¹. The maximum observed shift is $\Delta\omega/\omega = 0.54\%$. The dashed curve represents calculated shifts obtained from a Fourier modal method calculation without freely adjustable parameters that includes two-photon absorption and the Drude model for free carriers, in good agreement with experiment.

into account.

We have presented ultrafast all-optical switching measurements of thin Si woodpile photonic band gap crystals at telecom frequencies. The optical properties of a switched photonic crystal are for the first time probed as a continuous function of both frequency and delay time (see Fig. 3). These features allow us to observe at short times a narrowing of the

gap and at longer times of 1 ps a blue-shift of the gap. In other words, the blue edge of the gap shifts to lower frequency within the duration of the pulse, and subsequently shifts to higher frequency compared to the unswitched situation while the red edge only shifts to higher frequency. Consequently, the density of states near the blue edge of the band gap behaves more complex than predicted [5]: instead of single jumps as a function of time, multiple jumps could occur with time differences governed by the duration of the pump pulse. Clearly, versatile temporal control of the photonic density of states is expected to open exciting opportunities both in fundamental physics and in advanced applications.

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- [9] The intensity of each pump and probe pulse is monitored by two InG aA s photodiodes. The re ectivity signal is measured by a third photodiode (InG aA s or InA s). A boxcar averager holds the short output pulses of each detector for 1 m s, allowing simultaneous acquisition of separate pulse events of all three detector channels. Both pump and probe beam pass through a chopper whose frequency is synchronized to the repetition rate $f = 1$ kHz of the laser. The alignment of the two beams on the chopper blade is such that each millisecond, pump and probe beam are blocked or unblocked in a different permutation. In one sequence of four consecutive laser pulses, both pumped re ectivity, linear re ectivity, and two background measurements are collected. The pump-probe delay was set by a 40 cm long delay line with a resolution of 10 fs. At each frequency-delay setting, all detector signals from 4×250 pulse events were collected and stored to further increase the signal-to-noise ratio. From the resulting large data set, background was subtracted, and each re ectance signal was referenced to the corresponding monitor signal to compensate for intensity variations in the output of the laser.
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